



N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Low On-Resistance: R_{DS(ON)}
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 2 and 4)

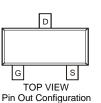
Mechanical Data

- Case: SOT-23
- Case Material: UL Flammability Classification Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020D
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)

SOT-23



TOP VIEW



Maximum Ratings $@T_A = 25^{\circ}C$ unless otherwise specified

Charae	cteristic	Symbol	Value	Units
Drain-Source Voltage		V _{DSS}	60	V
Drain-Gate Voltage R _{GS} ≤ 1.0MΩ	1	V _{DGR}	60	V
Gate-Source Voltage	Continuous Pulsed	V _{GSS}	±20 ±40	V
Drain Current	Continuous	I _D	240	mA

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	PD	300	mW
Thermal Resistance, Junction to Ambient	$R_{ ext{ heta}JA}$	417	°C/W
Operating and Storage Temperature Range	Tj, T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Symphol	Mim	Turn	Max	الم ال	Test Condition
		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 3)					-		1
Drain-Source Breakdown Voltage		BV _{DSS}	60	70	—	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	@ $T_{C} = 25^{\circ}C$	Inco			1.0	μA	$V_{DS} = 60V, V_{GS} = 0V$
Ŭ	@ T _C = 125°C	IDSS			500	μ. ι	$v_{\rm DS} = 00v$, $v_{\rm GS} = 0v$
Gate-Body Leakage		I _{GSS}			±10	nA	$V_{GS} = \pm 15V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 3)							
Gate Threshold Voltage		V _{GS(th)}	1.0		2.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
Static Drain-Source On-Resistance	@ T _J = 25°C	R _{DS (ON)}	_	1.6	3	Ω	$V_{GS} = 10V, I_{D} = 250mA$
		TOS (ON)		2.0	4		V _{GS} = 4.5V, I _D = 200mA
On-State Drain Current		I _{D(ON)}	0.8	1.0	_	Α	V _{GS} = 10V, V _{DS} = 7.5V
Forward Transconductance		g fs	80	_	_	mS	V _{DS} =10V, I _D = 0.2A
DYNAMIC CHARACTERISTICS							
Input Capacitance		Ciss		22	50	pF	
Output Capacitance		Coss	_	11	25	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance		C _{rss}	_	2.0	5.0	pF	
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		t _{D(ON)}	_	7.0	20	ns	$V_{DD} = 30V, I_D = 0.2A,$
Turn-Off Delay Time		t _{D(OFF)}		11	20	ns	$R_L = 150\Omega$, $V_{GEN} = 10V$, $R_{GEN} = 25\Omega$

Notes: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

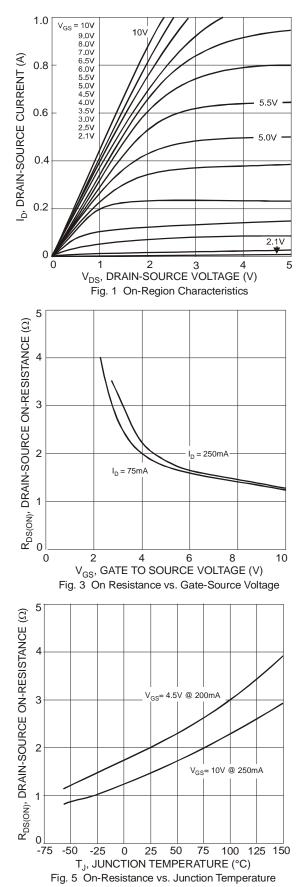
2. No purposefully added lead. Halogen and Antimony Free.

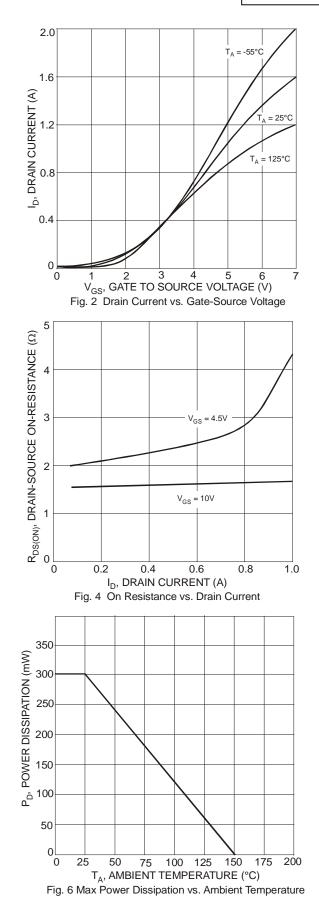
3. Short duration pulse test used to minimize self-heating effect.

 Product manufactured with Data Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or Sb203 Fire Retardants.



2N7002E





NEW PRODUCT

2N7002E Document number: DS30376 Rev. 7 - 2

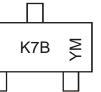


Ordering Information (Note 5)

Part Number	Case	Packaging
2N7002E-7-F	SOT-23	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

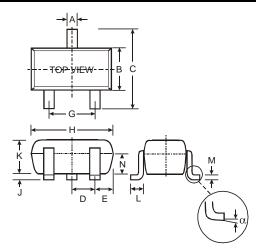


K7B = Product Type Marking Code YM = Date Code Marking Y = Year ex: P = 2003 M = Month ex: 9 = September

Date	Code	Kev

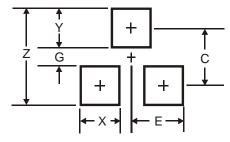
Year	2003	2004	20	05	2006	2007	2008	2009) 2	010	2011	2012
Code	Р	R	S	S	Т	U	V	W		Х	Y	Z
Month	Jan	Feb	Mar	Ар	r May	Jun	Jul	Aug	Sep	Oc	t Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Package Outline Dimensions



SOT-23					
Dim	Min	Max			
Α	0.37	0.51			
В	1.20	1.40			
С	2.30	2.50			
D	D 0.89 1.03				
E	0.60				
G	1.78	2.05			
Н	2.80	3.00			
J	0.013	0.10			
K	1.10				
L	L 0.45 0.61				
М	M 0.085 0.18				
Ν	N				
α	0°	8°			
All Dir	All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.4
G	0.7
Х	0.9
Y	1.4
С	2.0
E	0.9

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